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6/25/03
MollerPATENT
3885-0103P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Yoshinobu ONO et al. Conf.: 2546
Appl. No.: 10/046,741 Group: 2815
Filed: January 17, 2002 Examiner: S. Mulpuri
For: METHOD FOR FABRICATING III-V COMPOUND
SEMICONDUCTOR

RECEIVED
JUN 23 2003
TECHNOLOGY CENTER 2800REPLY UNDER 37 C.F.R. § 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

June 19, 2003

Sir:

In reply to the Office Action dated December 20, 2003, the due date having been extended three (3) months, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS

B1 --7. (New) A method for fabricating a III-V Group compound semiconductor comprising a step of on a flat GaAs substrate by epitaxial growth an $Al_{yj}Ga_{1-yj}As$ multiplayer structure ($0 \leq yj < 1$, j